



SDI Review Form 1.6

Journal Name:	Physical Science International Journal
Manuscript Number:	2015_PSIJ_18362
Title of the Manuscript:	Diffusion and trapping of positrons in unimplanted and ion-implanted 3C-SiC and 6H-SiC
Type of the Article	Original Research Article

General guideline for Peer Review process:

This journal's peer review policy states that **NO** manuscript should be rejected only on the basis of '**lack of Novelty**', provided the manuscript is scientifically robust and technically sound.

To know the complete guideline for Peer Review process, reviewers are requested to visit this link:

(<http://www.sciencedomain.org/page.php?id=sdi-general-editorial-policy#Peer-Review-Guideline>)



SDI Review Form 1.6

PART 1: Review Comments

	Reviewer's comment	Author's comment (if agreed with reviewer, correct the manuscript and highlight that part in the manuscript. It is mandatory that authors should write his/her feedback here)
Compulsory REVISION comments	<p>1. Author has compared calculated S-parameter result to experimental findings in each case. However, a comparison between the implanted and un-implanted calculated S-parameters for each case needs to be carried out, as this will give the paper better coverage than earlier researches in the field.</p> <p>2. Author needs to broaden discussion for each of the result obtained. Author discussion on results is too general.</p> <p>3. The diffusion of positrons into both implanted and un-implanted SiC is not discussed anywhere in the work. The title do not match the work carried out by the author. Re-phrasing is necessary to capture the work carried out. Author may wish to consider rephrasing the title to;</p> <p>“DETERMINATION OF S-PARAMETER FOR UNIMPLANTED AND ION IMPLANTED 3C-SiC AND 6H-SiC POSITRONS USING DIFFUSION TRAPPING MODEL”</p>	<p>1-2. We have added more explanation in Results and Discussion part. However, there is scope for future studies to calculate the fraction of positrons in trapping centres, lifetime components and mean positron lifetime, variation of diffusion length as function of mean penetration depth of positrons.</p> <p>3. The rate equations are written and solved by considering the diffusion of positrons at the surface of SiC and trapping into as-grown and irradiation induced defects.</p> <p>The title suggested by referee is more appropriate, thus, title of the paper is modified in revised manuscript as “Determination of S-parameter for unimplanted and ion-implanted 3C-SiC and 6H-SiC using diffusion trapping model”</p>



SDI Review Form 1.6

	<p>Author argument on results are not supported by any citation. In text citations are needed to support your arguments.</p> <p>Source(s) of all equations in the article should be referenced with all terms defined.</p>	<p>Further references have been added in support of results and discussion.</p> <p>One dimensional diffusion equation and rate equations are cited in revised manuscript.</p>
<u>Minor</u> REVISION comments	<p>The article is of high standard but author needs to follow the review comments to improve on the paper.</p>	<p>Improved as per suggestions.</p>
<u>Optional/General</u> comments		